

App. Serial No 10/539,224
Docket No.: BE020043US

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In the Specification:

Please amend Paragraph 0011 of the Specification as indicated below.

[0011] In another favorable modification a layer of the further semiconductor material, i.e. a polysilicon layer in the case of a silicon MOSFET ~~MOST~~, is deposited on the surface of the semiconductor body between the two heating steps. During the second thermal treatment this layer, which is e.g. 5 to 10 nm thick, acts as a source of silicon for the formation of e.g. CoSi_2 from the CoSi. Therefore, the deposition of this layer relieves constraints on the thickness of the poly-silicon consumable gate, i.e. the semiconductor silicon region of the gate. The unreacted part of e.g. the polysilicon layer is removed after the second heating step. This may be done either by a selective dry or wet etch or by oxidation and subsequent removal of the resulting oxide by an etching agent based on HF.